

Jiang Pu

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

33
papers

2,594
citations

16
h-index

41
g-index

41
ext. papers

2,968
ext. citations

11.6
avg, IF

5.04
L-index

#	Paper	IF	Citations
33	Nanowire-to-Nanoribbon Conversion in Transition-Metal Chalcogenides: Implications for One-Dimensional Electronics and Optoelectronics. <i>ACS Applied Nano Materials</i> , 2022 , 5, 1775-1782	5.6	2
32	Wafer-Scale Growth of One-Dimensional Transition-Metal Telluride Nanowires. <i>Nano Letters</i> , 2021 , 21, 243-249	11.5	8
31	Air-stable and efficient electron doping of monolayer MoS by salt-crown ether treatment. <i>Nanoscale</i> , 2021 , 13, 8784-8789	7.7	4
30	Electric Double Layer Doping of Charge-Ordered Insulators $\text{H}(\text{BEDT-TTF})_2\text{I}_3$ and $\text{H}(\text{BETS})_2\text{I}_3$. <i>Crystals</i> , 2021 , 11, 791	2.3	0
29	Room-Temperature Chiral Light-Emitting Diode Based on Strained Monolayer Semiconductors. <i>Advanced Materials</i> , 2021 , 33, e2100601	24	4
28	Room-Temperature Chiral Light-Emitting Diode Based on Strained Monolayer Semiconductors (Adv. Mater. 36/2021). <i>Advanced Materials</i> , 2021 , 33, 2170282	24	
27	Recent Progress on Light-Emitting Electrochemical Cells with Nonpolymeric Materials. <i>Advanced Functional Materials</i> , 2020 , 30, 1908641	15.6	14
26	2D Materials for Large-Area Flexible Thermoelectric Devices. <i>Advanced Energy Materials</i> , 2020 , 10, 1902842	8.42	72
25	Nonpolymeric LECs: Recent Progress on Light-Emitting Electrochemical Cells with Nonpolymeric Materials (Adv. Funct. Mater. 33/2020). <i>Advanced Functional Materials</i> , 2020 , 30, 2070223	15.6	
24	CVD growth of large-area InS atomic layers and device applications. <i>Nanoscale</i> , 2020 , 12, 9366-9374	7.7	3
23	Non-Fermi-liquid behavior and doping asymmetry in an organic Mott insulator interface. <i>Physical Review B</i> , 2019 , 100,	3.3	5
22	Electrolyte-Gating-Induced Metal-Like Conduction in Nonstoichiometric Organic Crystalline Semiconductors under Simultaneous Bandwidth Control. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019 , 13, 1900162	2.5	1
21	Two-dimensional ground-state mapping of a Mott-Hubbard system in a flexible field-effect device. <i>Science Advances</i> , 2019 , 5, eaav7282	14.3	13
20	Exciton Polarization and Renormalization Effect for Optical Modulation in Monolayer Semiconductors. <i>ACS Nano</i> , 2019 , 13, 9218-9226	16.7	3
19	Self-Aligned and Scalable Growth of Monolayer $\text{WSe}_2/\text{MoS}_2$ Lateral Heterojunctions. <i>Advanced Functional Materials</i> , 2018 , 28, 1706860	15.6	36
18	Synthesis of Large-Area InSe Monolayers by Chemical Vapor Deposition. <i>Small</i> , 2018 , 14, e1802351	11	48
17	Monolayer Transition Metal Dichalcogenides as Light Sources. <i>Advanced Materials</i> , 2018 , 30, e1707627	24	46

16	A Versatile and Simple Approach to Generate Light Emission in Semiconductors Mediated by Electric Double Layers. <i>Advanced Materials</i> , 2017 , 29, 1606918	24	31
15	Electron-hole doping asymmetry of Fermi surface reconstructed in a simple Mott insulator. <i>Nature Communications</i> , 2016 , 7, 12356	17.4	32
14	Thermoelectric Detection of Multi-Subband Density of States in Semiconducting and Metallic Single-Walled Carbon Nanotubes. <i>Small</i> , 2016 , 12, 3388-92	11	40
13	Highly Flexible and High-Performance Complementary Inverters of Large-Area Transition Metal Dichalcogenide Monolayers. <i>Advanced Materials</i> , 2016 , 28, 4111-9	24	90
12	Simultaneous enhancement of conductivity and Seebeck coefficient in an organic Mott transistor. <i>Applied Physics Letters</i> , 2016 , 109, 233301	3.4	9
11	Effects of electrolyte gating on photoluminescence spectra of large-area WSe ₂ monolayer films. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 06GB02	1.4	6
10	Photodetection in p-n junctions formed by electrolyte-gated transistors of two-dimensional crystals. <i>Applied Physics Letters</i> , 2016 , 109, 201107	3.4	12
9	Enhanced thermoelectric power in two-dimensional transition metal dichalcogenide monolayers. <i>Physical Review B</i> , 2016 , 94,	3.3	45
8	Charge transport in ion-gated mono-, bi-, and trilayer MoS ₂ field effect transistors. <i>Scientific Reports</i> , 2014 , 4, 7293	4.9	52
7	Large-area synthesis of highly crystalline WSe ₂ monolayers and device applications. <i>ACS Nano</i> , 2014 , 8, 923-30	16.7	732
6	Monolayer MoSe ₂ grown by chemical vapor deposition for fast photodetection. <i>ACS Nano</i> , 2014 , 8, 8582-8597	11.0	413
5	Flexible and stretchable thin-film transistors based on molybdenum disulphide. <i>Physical Chemistry Chemical Physics</i> , 2014 , 16, 14996-5006	3.6	50
4	Fabrication of stretchable MoS ₂ thin-film transistors using elastic ion-gel gate dielectrics. <i>Applied Physics Letters</i> , 2013 , 103, 023505	3.4	75
3	Semiconductors: Ambipolar Organic Single-Crystal Transistors Based on Ion Gels (Adv. Mater. 32/2012). <i>Advanced Materials</i> , 2012 , 24, 4463-4463	24	1
2	Highly flexible MoS ₂ thin-film transistors with ion gel dielectrics. <i>Nano Letters</i> , 2012 , 12, 4013-7	11.5	663
1	Ambipolar organic single-crystal transistors based on ion gels. <i>Advanced Materials</i> , 2012 , 24, 4392-7	24	75